

Micro Commercial Components 20736 Marilla Street Chatsworth CA 91311

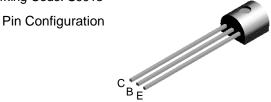
Phone: (818) 701-4933 (818) 701-4939 Fax:

S9013

Features

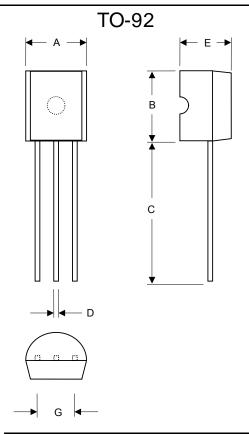
- TO-92 Plastic-Encapsulate Transistors
- Capable of 0.625Watts(Tamb=25°C) of Power Dissipation.
- Collector-current 0.5A
- Collector-base Voltage 40V

- Operating and storage junction temperature range: -55°C to +150°C
- Marking Code: S9013



Electrical Characteristics @ 25°C Unless Otherwise Specified									
Symbo	l	Parameter Min Max		Max	Units				
OFF CHARACTERISTICS									
$V_{(BR)CBO}$		Collector-Base Breakdown Voltage (l _c =100uAdc, l ₌ =0)		je	40)		Vdc	
$V_{(BR)CEO}$		Collector-Emitter Breakdown Voltage 25 (k=0.1mAdc, k=0)					Vdc		
$V_{(BR)EBO}$		r-Base Breakdown Voltage 5.0 100uAdc, I _C =0)				Vdc			
СВО		Collector Cutoff Current (V _{CB} =40Vdc, ξ =0)				-	0.1	uAdc	
I _{CEO}	Collecto	Collector Cutoff Current (V _{CE} =20Vdc, _k =0)				-	0.1	uAdc	
I _{EBO}		Emitter Cutoff Current (V _{EB} =5.0Vdc,				-	0.1	uAdc	
ON CHARACTERISTICS									
h _{FE(1)}		DC Current Gain (Ե=50mAdc, V _{CE} =1.0Vdc)			6-	4	300		
h _{FE(2)}	DC Cur	DC Current Gain ((L=500mAdc, V _{CE} =1.0Vdc)				0			
$V_{CE(sat)}$	Collecto	Collector-Emitter Saturation Voltage (b=500mAdc, b=50mAdc)						Vdc	
$V_{BE(sat)}$	Base-E	Base-Emitter Saturation Voltage (h=500mAdc, h=50mAdc)						Vdc	
V _{EB}	Base- Emitter Voltage (L=100mAdc)		ge				1.4	Vdc	
SMALL-S	IGNAL CHAR		CS	· ·				-	
f _T	Transis	tor Frequency OmAdc, V _{CE} =6.0Vdc, f=30MHz)		150			MHz		
CLASSIFI	CATION OF H								
Rank	E	F	G	F	Н		- 11		
Range	78-112	96-135	115-150	150-	150-180 180-		0-200	190-300	

NPN Silicon Transistors



DIMENSIONS											
	INC	HES	М								
DIM	MIN	MAX	MIN	MAX	NOTE						
Α	.175	.185	4.45	4.70							
В	.175	.185	4.46	4.70							
С	.500		12.7								
D	.016	.020	0.41	0.63							
Е	.135	.145	3.43	3.68							
G	.095	.105	2.42	2.67							

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